

Refine Search

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Terms	Documents
L6 and (lightly near2 doped)	13

Database:

US Pre-Grant Publication Full-Text Database
 US Patents Full-Text Database
 US OCR Full-Text Database
 EPO Abstracts Database
 JPO Abstracts Database
 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

Search:

L7

Search History

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result set

DB=USPT; PLUR=YES; OP=ADJ

<u>L7</u>	L6 and (lightly near2 doped)	13	<u>L7</u>
<u>L6</u>	L5 and (high adj voltage)	13	<u>L6</u>
<u>L5</u>	L3 and polysilicon and (silicide or salicide)	18	<u>L5</u>
<u>L4</u>	L3 and polysilicon and saliciding	0	<u>L4</u>
<u>L3</u>	L2 and (high adj K)	21	<u>L3</u>
<u>L2</u>	L1 and IMD	197	<u>L2</u>
<u>L1</u>	gate near2 electrodes	49881	<u>L1</u>

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☐ 1. Document ID: US 6686236 B2

L7: Entry 1 of 13

File: USPT

Feb 3, 2004

US-PAT-NO: 6686236

DOCUMENT-IDENTIFIER: US 6686236 B2

TITLE: Methods of preventing reduction of IrOx during PZT formation by metalorganic chemical vapor deposition or other processing

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMC	Draw D
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☐ 2. Document ID: US 6635528 B2

L7: Entry 2 of 13

File: USPT

Oct 21, 2003

US-PAT-NO: 6635528

DOCUMENT-IDENTIFIER: US 6635528 B2

**** See image for Certificate of Correction ****

TITLE: Method of planarizing a conductive plug situated under a ferroelectric capacitor

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMC	Draw D
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☐ 3. Document ID: US 6635498 B2

L7: Entry 3 of 13

File: USPT

Oct 21, 2003

US-PAT-NO: 6635498

DOCUMENT-IDENTIFIER: US 6635498 B2

TITLE: Method of patterning a FeRAM capacitor with a sidewall during bottom electrode etch

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMC	Draw D
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☐ 4. Document ID: US 6635497 B2

L7: Entry 4 of 13

File: USPT

Oct 21, 2003

US-PAT-NO: 6635497

DOCUMENT-IDENTIFIER: US 6635497 B2

TITLE: Methods of preventing reduction of IrOx during PZT formation by metalorganic chemical vapor deposition or other processing

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw Dc
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☐ 5. Document ID: US 6596547 B2

L7: Entry 5 of 13

File: USPT

Jul 22, 2003

US-PAT-NO: 6596547

DOCUMENT-IDENTIFIER: US 6596547 B2

TITLE: Methods of preventing reduction of IrOx during PZT formation by metalorganic chemical vapor deposition or other processing

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw Dc
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☐ 6. Document ID: US 6576546 B2

L7: Entry 6 of 13

File: USPT

Jun 10, 2003

US-PAT-NO: 6576546

DOCUMENT-IDENTIFIER: US 6576546 B2

TITLE: Method of enhancing adhesion of a conductive barrier layer to an underlying conductive plug and contact for ferroelectric applications

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw Dc
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☐ 7. Document ID: US 6548343 B1

L7: Entry 7 of 13

File: USPT

Apr 15, 2003

US-PAT-NO: 6548343

DOCUMENT-IDENTIFIER: US 6548343 B1

TITLE: Method of fabricating a ferroelectric memory cell

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw Dc
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☐ 8. Document ID: US 6534809 B2

L7: Entry 8 of 13

File: USPT

Mar 18, 2003

US-PAT-NO: 6534809

DOCUMENT-IDENTIFIER: US 6534809 B2

**** See image for Certificate of Correction ****

TITLE: Hardmask designs for dry etching FeRAM capacitor stacks

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWC	Draw Dc
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☐ 9. Document ID: US 6528386 B1

L7: Entry 9 of 13

File: USPT

Mar 4, 2003

US-PAT-NO: 6528386

DOCUMENT-IDENTIFIER: US 6528386 B1

TITLE: Protection of tungsten alignment mark for FeRAM processing

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWC	Draw Dc
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☐ 10. Document ID: US 6528328 B1

L7: Entry 10 of 13

File: USPT

Mar 4, 2003

US-PAT-NO: 6528328

DOCUMENT-IDENTIFIER: US 6528328 B1

TITLE: Methods of preventing reduction of irox during PZT formation by metalorganic chemical vapor deposition or other processing

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWC	Draw Dc
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Terms	Documents
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☐ 11. Document ID: US 6500678 B1

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File: USPT

Dec 31, 2002

US-PAT-NO: 6500678

DOCUMENT-IDENTIFIER: US 6500678 B1

TITLE: Methods of preventing reduction of IrOx during PZT formation by metalorganic chemical vapor deposition or other processing

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWIC	Draw D
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☐ 12. Document ID: US 6492222 B1

L7: Entry 12 of 13

File: USPT

Dec 10, 2002

US-PAT-NO: 6492222

DOCUMENT-IDENTIFIER: US 6492222 B1

TITLE: Method of dry etching PZT capacitor stack to form high-density ferroelectric memory devices

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWIC	Draw D
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☐ 13. Document ID: US 6485988 B2

L7: Entry 13 of 13

File: USPT

Nov 26, 2002

US-PAT-NO: 6485988

DOCUMENT-IDENTIFIER: US 6485988 B2

TITLE: Hydrogen-free contact etch for ferroelectric capacitor formation

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWIC	Draw D
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Terms	Documents
L6 and (lightly near2 doped)	13

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